

500 mA, Fixed-Output, CMOS LDO with Shutdown

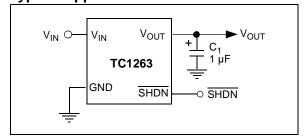
Features

- · Very Low Dropout Voltage
- 500 mA Output Current
- High-Output Voltage Accuracy
- · Standard or Custom Output Voltages
- Overcurrent and Overtemperature Protection
- SHDN Input for Active Power Management
- ERROR Output Can Be Used as a Low Battery Detector (SOIC only)

Applications

- · Battery-Operated Systems
- Portable Computers
- Medical Instruments
- Instrumentation
- Cellular/GSM/PHS Phones
- · Linear Post-Regulators for SMPS
- Pagers

Typical Application



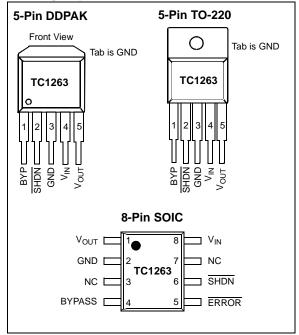
Description

The TC1263 is a fixed-output, high-accuracy (typically $\pm 0.5\%$) CMOS low dropout regulator. Designed specifically for battery-operated systems, the TC1263's CMOS construction eliminates wasted ground current, significantly extending battery life. Total supply current is typically 80 μ A at full load (20 to 60 times lower than in bipolar regulators).

TC1263 key features include ultra low noise operation, very low dropout voltage (typically 350 mV at full load) and fast response to step changes in load.

The TC1263 incorporates both overtemperature and overcurrent protection. The TC1263 is stable with an output capacitor of only 1 μ F and has a maximum output current of 500 mA. It is available in 8-Pin SOIC, 5-Pin TO-220 and 5-Pin DDPAK packages.

Package Type



1.0 ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings †

 † Notice: Stresses above those listed under "Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at those or any other conditions above those indicated in the operation listings of this specification is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability.

DC CHARACTERISTICS

Electrical Specifications: Unless otherwise indicated, $V_{IN} = V_R + 1.0V$, (Note 1), $I_L = 100 \mu A$, $C_L = 3.3 \mu F$, $\overline{SHDN} > V_{IH}$, $T_A = +25^{\circ}C$. Boldface type specifications apply for junction temperatures of -40°C to +125°C.

SHDN > V_{IH} , $I_{\text{A}} = +25^{\circ}\text{C}$. Boldface type specifications apply for junction temperatures of -40°C to +125°C.									
Parameters	Sym	Min	Тур	Max	Units	Conditions			
Input Operating Voltage	V _{IN}	2.7		6.0	V	Note 2			
Maximum Output Current	I _{OUTMAX}	500	1	_	mA				
Output Voltage	V _{OUT}	V _R – 2.5%	V _R ± 0.5%	V _R + 2.5%	V	Note 1			
V _{OUT} Temperature Coefficient	$\Delta V_{OUT}/\Delta T$	1	40		ppm/°C	Note 3			
Line Regulation	$\Delta V_{OUT}/\Delta V_{IN}$	1	0.05	0.35	%	$(V_R + 1V) \le V_{IN} \le 6V$			
Load Regulation (Note 4)	$\Delta V_{OUT}/V_{OUT}$	-0.01	0.002	+0.01	%/mA	$I_L = 0.1 \text{ mA to } I_{OUTMAX}$			
Dropout Voltage (Note 5)	V_{IN} - V_{OUT}	1	20	30	mV	I _L = 100 μA			
		1	60	130		I _L = 100 mA			
		1	200	390		I _L = 300 mA			
		1	350	650		I _L = 500 mA			
Supply Current	I _{DD}	1	80	130	μΑ	$\overline{SHDN} = V_{IH}, I_L = 0$			
Shutdown Supply Current	I _{SHDN}	1	0.05	1	μΑ	SHDN = 0V			
Power Supply Rejection Ratio	PSRR	1	64		db	F ≤ 1 kHz			
Output Short Circuit Current	l _{outsc}		1200	1400	mA	V _{OUT} = 0V			
Thermal Regulation	$\Delta V_{OUT}/\Delta P_{D}$		0.04		V/W	Note 6			
Output Noise	eN	_	260	_	nV/√Hz	I _L = I _{OUTMAX} , F = 10 kHz			

- **Note 1:** V_R is the regulator output voltage setting.
 - 2: The minimum V_{IN} has to justify the conditions: $V_{IN} \ge V_R + V_{DROPOUT}$ and $V_{IN} \ge 2.7V$ for $I_L = 0.1$ mA to I_{OUTMAX} .

3:
$$TCV_{OUT} = \frac{(V_{OUTMAX} - V_{OUTMIN}) - 10^6}{V_{OUT} \times \Delta T}$$

- 4: Regulation is measured at a constant junction temperature using low duty-cycle pulse testing. Load regulation is tested over a load range from 0.1 mA to the maximum specified output current. Changes in output voltage due to heating effects are covered by the thermal regulation specification.
- 5: Dropout voltage is defined as the input-to-output differential at which the output voltage drops 2% below its nominal value measured at a 1.0V differential.
- 6: Thermal regulation is defined as the change in output voltage at a time T after a change in power dissipation is applied, excluding load or line regulation effects. Specifications are for a current pulse equal to I_{LMAX} at V_{IN} = 6V for T = 10 ms.
- 7: The maximum allowable power dissipation is a function of ambient temperature, the maximum allowable junction temperature and the thermal resistance from junction-to-air (i.e., T_A, T_J, θ_{JA}). Exceeding the maximum allowable power dissipation causes the device to initiate thermal shutdown. Please see Section 5.0 "Thermal Considerations" for more details.

DC CHARACTERISTICS (CONTINUED)

Electrical Specifications: Unless SHDN > V _{IH} , T _A = +25°C. Boldface				, _		•
Parameters	Sym	Min	Тур	Max	Units	Conditions
SHDN Input		•	<u>'</u>		•	
SHDN Input High Threshold	V _{IH}	45	_	_	%V _{IN}	
SHDN Input Low Threshold	V _{IL}	_	_	15	%V _{IN}	
ERROR Output (SOIC Only)						
Minimum Operating Voltage	V _{MIN}	1.0	_	_	V	
Output Logic Low Voltage	V _{OL}	_	_	400	mV	1 mA Flows to ERROR
ERROR Threshold Voltage	V _{TH}	_	0.95 x V _R	_	V	
FRROR Positive Hysteresis	Vuivo	_	50	_	mV	

- **Note 1:** V_R is the regulator output voltage setting.
 - 2: The minimum V_{IN} has to justify the conditions: $V_{IN} \ge V_R + V_{DROPOUT}$ and $V_{IN} \ge 2.7V$ for $I_L = 0.1$ mA to I_{OUTMAX} .

3:
$$TCV_{OUT} = \frac{\left(V_{OUTMAX} - V_{OUTMIN}\right) - 10^6}{V_{OUT} \times \Delta T}$$

- 4: Regulation is measured at a constant junction temperature using low duty-cycle pulse testing. Load regulation is tested over a load range from 0.1 mA to the maximum specified output current. Changes in output voltage due to heating effects are covered by the thermal regulation specification.
- 5: Dropout voltage is defined as the input-to-output differential at which the output voltage drops 2% below its nominal value measured at a 1.0V differential.
- 6: Thermal regulation is defined as the change in output voltage at a time T after a change in power dissipation is applied, excluding load or line regulation effects. Specifications are for a current pulse equal to I_{LMAX} at V_{IN} = 6V for T = 10 ms.
- 7: The maximum allowable power dissipation is a function of ambient temperature, the maximum allowable junction temperature and the thermal resistance from junction-to-air (i.e., T_A, T_J, θ_{JA}). Exceeding the maximum allowable power dissipation causes the device to initiate thermal shutdown. Please see Section 5.0 "Thermal Considerations" for more details.

TEMPERATURE CHARACTERISTICS

Electrical Specifications: Unless otherwise indicated, $V_{IN} = V_R + 1.0V$, $I_L = 100$ μA, $C_L = 3.3$ μF, $\overline{SHDN} > V_{IH}$, $T_A = +25$ °C.									
Parameters	Sym	Min	Тур	Max	Units	Conditions			
Temperature Ranges									
Specified Temperature Range	T _A	-40		+125	°C	Note 1			
Operating Temperature Range	T_J	-40	_	+125	°C				
Storage Temperature Range	T _A	-65	_	+150	°C				
Thermal Package Resistances									
Thermal Resistance, 5L-DDPAK	θ_{JA}	_	57	_	°C/W				
Thermal Resistance, 5L-TO-220	θ_{JA}	_	71	_	°C/W				
Thermal Resistance, 8L-SOIC	θ_{JA}		163		°C/W				

Note 1: Operation in this range must not cause T_J to exceed Maximum Junction Temperature (+125°C).

2.0 TYPICAL PERFORMANCE CURVES

Note: The graphs and tables provided following this note are a statistical summary based on a limited number of samples and are provided for informational purposes only. The performance characteristics listed herein are not tested or guaranteed. In some graphs or tables, the data presented may be outside the specified operating range (e.g., outside specified power supply range) and therefore outside the warranted range.

Note: Unless otherwise indicated, $V_{IN} = V_R + 1.0V$, $I_L = 100 \mu A$, $C_L = 3.3 \mu F$, $\overline{SHDN} > V_{IH}$, $T_A = +25$ °C.

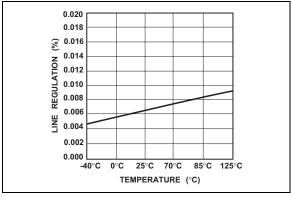


FIGURE 2-1: Line Regulation vs. Temperature.

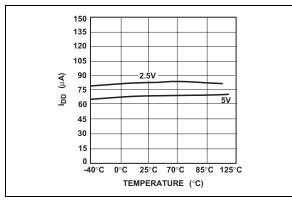


FIGURE 2-4: I_{DD} vs. Temperature.

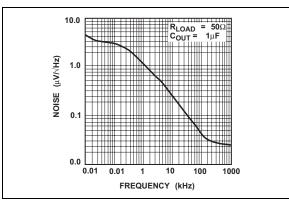


FIGURE 2-2: Output Noise vs. Frequency.

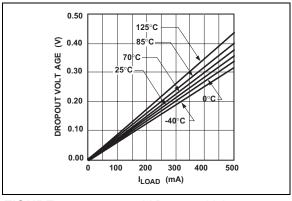


FIGURE 2-5: 2.5V Dropout Voltage vs. I_{LOAD} .

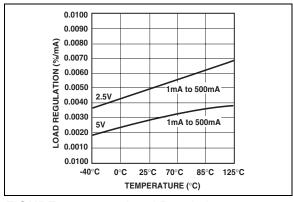


FIGURE 2-3: Load Regulation vs. Temperature.

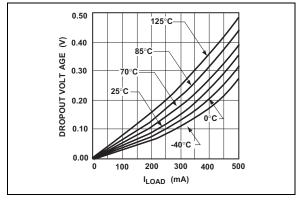


FIGURE 2-6: 5.0V Dropout Voltage vs. I_{LOAD} .

Note: Unless otherwise indicated, V_{IN} = V_R + 1.0V, I_L = 100 μ A, C_L = 3.3 μ F, \overline{SHDN} > V_{IH} , T_A = +25°C.

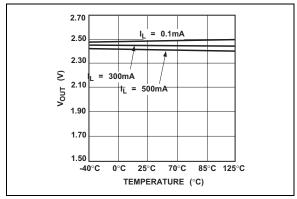


FIGURE 2-7: 2.5V V_{OUT} vs. Temperature.

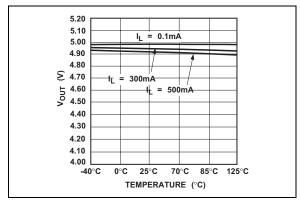


FIGURE 2-8: 5.0V V_{OUT} vs. Temperature.

3.0 PIN DESCRIPTIONS

The descriptions of the pins are listed in Table 3-1.

TABLE 3-1: PIN FUNCTION TABLE

Pin No. (8-Pin SOIC)	Pin No. (5-Pin DDPAK) (5-Pin TO-220)	Symbol	Description
1	5	V _{OUT}	Regulated voltage output
2	3	GND	Ground terminal
3	_	NC	No connect
4	1	BYPASS	Reference bypass input
5	_	ERROR	Out-of-Regulation Flag (open-drain output).
6	2	SHDN	Shutdown control input
7	_	NC	No connect
8	4	V_{IN}	Unregulated supply input

3.1 Regulated Output Voltage (V_{OUT})

V_{OUT} is a regulated voltage output.

3.2 Ground (GND)

Ground terminal.

3.3 Reference Bypass (BYPASS)

Reference bypass input. Connect a 470 pF to the BYPASS input to further reduce output noise.

3.4 Out-of-Regulation Flag (ERROR)

Out-of-Regulation Flag (open-drain output). $\overline{\text{ERROR}}$ goes low when V_{OUT} is out-of-tolerance by approximately – 5%.

3.5 Shutdown Control (SHDN)

Shutdown control input. The regulator is fully enabled when a logic-high is applied to \overline{SHDN} . The regulator enters shutdown when a logic-low is applied to this input. During shutdown, output voltage falls to zero and supply current is reduced to $0.05~\mu A$ (typical).

3.6 Unregulated Supply (V_{IN})

V_{IN} is an unregulated supply input.

4.0 DETAILED DESCRIPTION

The TC1263 is a precision, fixed-output LDO. Unlike bipolar regulators, the TC1263's supply current does not increase with load current. In addition, V_{OUT} remains stable and within regulation over the entire 0 mA to $I_{LOADMAX}$ load current range (an important consideration in RTC and CMOS RAM battery back-up applications).

Figure 4-1 shows a typical application circuit.

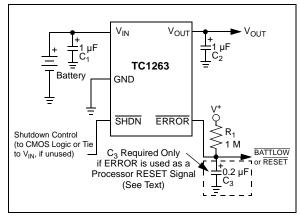


FIGURE 4-1: Typical Application Circuit.

4.1 Output Capacitor

A $1 \mu F$ (min.) capacitor from V_{OUT} to ground is required. The output capacitor should have an Effective Series Eesistance (ESR) greater than 0.1Ω and less than 5Ω . A 1 μ F capacitor should be connected from V_{IN} to GND if there is either more than 10 inches of wire between the regulator and the AC filter capacitor or a battery is used as the power source. Aluminum electrolytic or tantalum capacitor types can be used. Since many aluminum electrolytic capacitors freeze at approximately -30°C, solid tantalums recommended for applications operating below -25°C. When operating from sources other than batteries, supply-noise rejection and transient response can be improved by increasing the value of the input and output capacitors, and by employing passive filtering techniques.

4.2 ERROR Output

 $\overline{\text{ERROR}}$ is driven low whenever V_OUT falls out of regulation by more than – 5% (typ.). This condition may be caused by low input voltage, output current limiting or thermal limiting. The $\overline{\text{ERROR}}$ threshold is 5% below rated V_OUT, regardless of the programmed output voltage value (e.g., $\overline{\text{ERROR}}$ = V_OL at 4.75V (typ.) for a 5.0V regulator and 2.85V (typ.) for a 3.0V regulator). $\overline{\text{ERROR}}$ output operation is shown in Figure 4-2.

Note that $\overline{\text{ERROR}}$ is active when V_{OUT} is at or below V_{TH} , and inactive when V_{OUT} is above V_{TH} + V_{HYS} .

As shown in Figure 4-1, $\overline{\text{ERROR}}$ can be used as a battery-low flag or as a processor $\overline{\text{RESET}}$ signal (with the addition of timing capacitor C₃). R₁ x C₃ should be chosen to maintain $\overline{\text{ERROR}}$ below V_{IH} of the processor $\overline{\text{RESET}}$ input for at least 200 ms to allow time for the system to stabilize. Pull-up resistor R₁ can be tied to V_{OUT}, V_{IN} or any other voltage less than (V_{IN} + 0.3V).

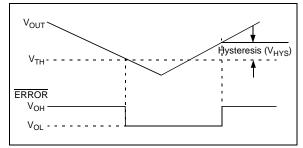


FIGURE 4-2: ERROR Output Operation.

5.0 THERMAL CONSIDERATIONS

5.1 Thermal Shutdown

Integrated thermal protection circuitry shuts the regulator off when the die temperature exceeds 160°C. The regulator remains off until the die temperature drops to approximately 150°C.

5.2 Power Dissipation

The amount of power the regulator dissipates is primarily a function of input and output voltage and output current. The following equation is used to calculate worst-case actual power dissipation:

EQUATION 5-1:

$$P_D = (V_{INMAX} - V_{OUTMIN})I_{LOADMAX}$$

Where:

P_D = Worst-case actual power dissipation

 V_{INMAX} = Maximum voltage on V_{IN}

V_{OUTMIN} = Minimum regulator output voltage

I_{LOADMAX} = Maximum output (load) current

The maximum allowable power dissipation (Equation 5-2) is a function of the maximum ambient temperature (T_{AMAX}), the maximum allowable die temperature (T_{JMAX}) and the thermal resistance from junction-to-air (θ_{JA}).

EQUATION 5-2:

$$P_{DMAX} = \frac{T_{JMAX} - T_{AMAX}}{\Theta_{IA}}$$

P_D = Worst-case actual power dissipation

 V_{INMAX} = Maximum voltage on V_{IN}

V_{OUTMIN} = Minimum regulator output voltage

I_{LOADMAX} = Maximum output (load) current

Table 5-1 and Table 5-2 show various values of θ_{JA} for the TC1263 package types.

TABLE 5-1: THERMAL RESISTANCE
GUIDELINES FOR TC1263 IN
8-PIN SOIC PACKAGE

Copper Area (Topside)*	Copper Area (Backside)	Board Area	$\begin{array}{c} \textbf{Thermal} \\ \textbf{Resistance} \\ (\theta_{JA}\textbf{)} \end{array}$
2500 sq mm	2500 sq mm	2500 sq mm	60°C/W
1000 sq mm	2500 sq mm	2500 sq mm	60°C/W
225 sq mm	2500 sq mm	2500 sq mm	68°C/W
100 sq mm	2500 sq mm	2500 sq mm	74°C/W

^{*} Pin 2 is ground. Device is mounted on top-side.

TABLE 5-2: THERMAL RESISTANCE GUIDELINES FOR TC1263 IN 5-PIN DDPAK/TO-220 PACKAGE

Copper Area (Topside)*	Copper Area (Backside)	Board Area	Thermal Resistance (θ _{JA})	
2500 sq mm	2500 sq mm	2500 sq mm	25°C/W	
1000 sq mm	2500 sq mm	2500 sq mm	27°C/W	
125 sq mm	2500 sq mm	2500 sq mm	35°C/W	

^{*} Tab of device attached to top-side copper

Equation 5-1 can be used in conjunction with Equation 5-2 to ensure regulator thermal operation is within limits. For example:

Given:

 V_{INMAX} = 3.3V ± 10% V_{OUTMIN} = 2.7V ± 0.5% $I_{LOADMAX}$ = 275 mA T_{JMAX} = 125°C T_{AMAX} = 95°C θ_{JA} = 60° C/W (SOIC)

Find:

- 1. Actual power dissipation
- 2. Maximum allowable dissipation

Actual power dissipation:

$$P_D \approx (V_{INMAX} - V_{OUTMIN})I_{LOADMAX}$$

 $P_D = (3.3 \times 1.1) - (2.7 \times .995)275 \times 10^{-3}$
 $P_D = 260 \text{ mW}$

Maximum allowable power dissipation:

$$P_{DMAX} = \frac{T_{JMAX} - T_{AMAX}}{\theta_{JA}}$$

$$P_{DMAX} = \frac{(125 - 95)}{60}$$

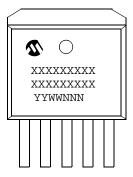
$$P_{DMAX} = 500 \text{ mW}$$

In this example, the TC1263 dissipates a maximum of 260 mW below the allowable limit of 500 mW. In a similar manner, Equation 5-1 and Equation 5-2 can be used to calculate maximum current and/or input voltage limits. For example, the maximum allowable V_{IN} is found by substituting the maximum allowable power dissipation of 500 mW into Equation 5-1, from which $V_{INMAX} = 4.6V$.

6.0 PACKAGING INFORMATION

6.1 Package Marking Information

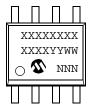
5-Lead DDPAK



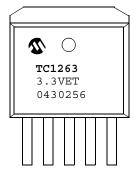
5-Lead TO-220



8-Lead SOIC (150 mil)



Example:



Example:







Legend: XX...X Customer-specific information

Y Year code (last digit of calendar year)
YY Year code (last 2 digits of calendar year)
WW Week code (week of January 1 is week '01')

NNN Alphanumeric traceability code

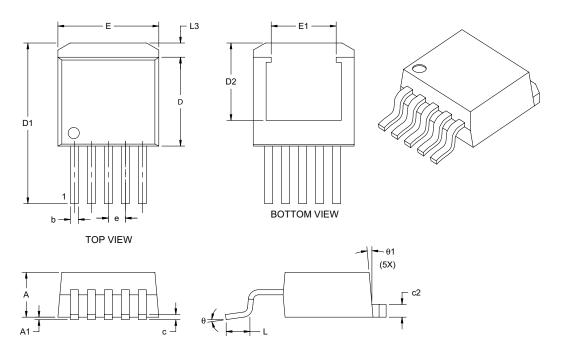
(e3) Pb-free JEDEC designator for Matte Tin (Sn)

This package is Pb-free. The Pb-free JEDEC designator (e3)

can be found on the outer packaging for this package.

Note: In the event the full Microchip part number cannot be marked on one line, it will be carried over to the next line, thus limiting the number of available characters for customer-specific information.

5-Lead Plastic (ET) (DDPAK)



		INCHES*			MILLIMETERS		
Dimension	MIN	NOM	MAX	MIN	NOM	MAX	
Number of Pins			5			5	
Pitch	е		.067 BSC			1.70 BSC	
Overall Height	Α	.170	.177	.183	4.32	4.50	4.65
Standoff §	A1	.000	.005	.010	0.00	0.13	0.25
Overall Width	E	.385	.398	.410	9.78	10.11	10.41
Exposed Pad Width	E1		.256 REF		6.50 REF		
Molded Package Length	D	.330	.350	.370	8.38	8.89	9.40
Overall Length	D1	.549	.577	.605	13.94	14.66	15.37
Exposed Pad Length	D2		.303 REF		7.75 REF		
Lead Thickness	С	.014	.020	.026	0.36	0.51	0.66
Pad Thickness	c2	.045		.055	1.14		1.40
Lead Width	b	.026	.032	.037	0.66	0.81	0.94
Foot Length	L	.068	.089	.110	1.73	2.26	2.79
Pad Length	L3	.045		.067	1.14		1.70
Foot Angle	θ	1		8°	1		8°
Mold Draft Angle	θ1	3°		7°	3°		7°

^{*}Controlling Parameter

Notes

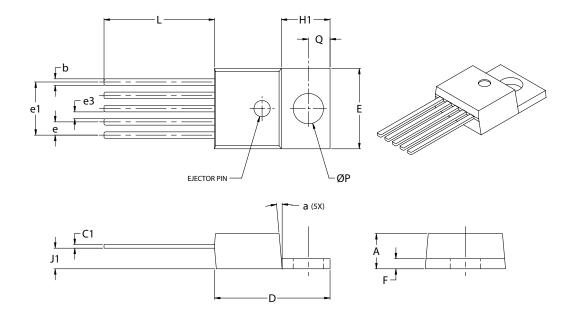
Dimensions D and E do not include mold flash or protrusions. Mold flash or protrusions shall not exceed .010" (0.254mm) per side.

JEDEC equivalent: TO-252

Drawing No. C04-012

[§] Significant Characteristic

5-Lead Plastic Transistor Outline (AT) (TO-220)



	Units Dimension Limits		ES*	MILLIMETERS		
Dimension			MAX	MIN	MAX	
Lead Pitch	e	.060	.072	1.52	1.83	
Overall Lead Centers	e1	.263	.273	6.68	6.93	
Space Between Leads	e3	.030	.040	0.76	1.02	
Overall Height	А	.160	.190	4.06	4.83	
Overall Width	E	.385	.415	9.78	10.54	
Overall Length	D	.560	.590	14.22	14.99	
Flag Length	H1	.234	.258	5.94	6.55	
Flag Thickness	F	.045	.055	1.14	1.40	
Through Hole Center	Q	.103	.113	2.62	2.87	
Through Hole Diameter	P	.146	.156	3.71	3.96	
Lead Length	L	.540	.560	13.72	14.22	
Base to Bottom of Lead	J1	.090	.115	2.29	2.92	
Lead Thickness	C1	.014	.022	0.36	0.56	
Lead Width	b	.025	.040	0.64	1.02	
Mold Draft Angle	a	3°	7°	3°	7°	

^{*}Controlling Parameter

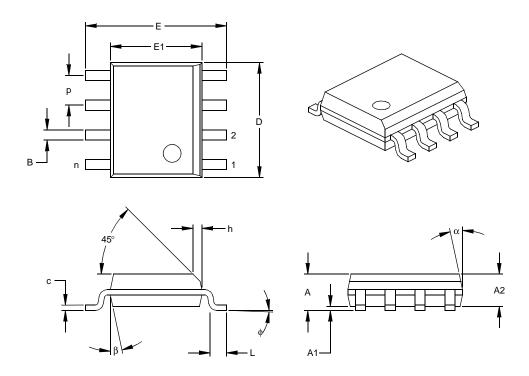
Notes:

Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed .010" (0.254mm) per side.

JEDEC equivalent: TO-220

Drawing No. C04-036

8-Lead Plastic Small Outline (SN) - Narrow, 150 mil Body (SOIC)



	Units	Units INCHES*			N	MILLIMETERS		
Dimension	MIN	NOM	MAX	MIN	NOM	MAX		
Number of Pins	n		8			8		
Pitch	р		.050			1.27		
Overall Height	Α	.053	.061	.069	1.35	1.55	1.75	
Molded Package Thickness	A2	.052	.056	.061	1.32	1.42	1.55	
Standoff §	A1	.004	.007	.010	0.10	0.18	0.25	
Overall Width	Е	.228	.237	.244	5.79	6.02	6.20	
Molded Package Width	E1	.146	.154	.157	3.71	3.91	3.99	
Overall Length	D	.189	.193	.197	4.80	4.90	5.00	
Chamfer Distance	h	.010	.015	.020	0.25	0.38	0.51	
Foot Length	L	.019	.025	.030	0.48	0.62	0.76	
Foot Angle	ф	0	4	8	0	4	8	
Lead Thickness	С	.008	.009	.010	0.20	0.23	0.25	
Lead Width	В	.013	.017	.020	0.33	0.42	0.51	
Mold Draft Angle Top	α	0	12	15	0	12	15	
Mold Draft Angle Bottom	β	0	12	15	0	12	15	

Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed

.010" (0.254mm) per side.
JEDEC Equivalent: MS-012
Drawing No. C04-057

^{*} Controlling Parameter § Significant Characteristic

APPENDIX A: REVISION HISTORY

Revision C (January 2005)

The following is the list of modifications:

- 1. Changes to DC Characteristics table
- 2. Added Appendix A: Revision History.

Revision B (May 2002)

No information for this revision.

Revision A (March 2002)

Original data sheet release.

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NOTES:

PRODUCT IDENTIFICATION SYSTEM

To order or obtain information, e.g., on pricing or delivery, refer to the factory or the listed sales office.

PART NO.	<u>X.X</u>	<u> </u>	<u>xx</u>	XX	Exa	mples:	
	 Voltage Option	Temperature Range	 Package	Tape and Reel	a) b) c)	TC1263-2.5VAT TC1263-2.8VAT TC1263-3.0VAT TC1263-3.3VAT	2.5V LDO, TO-220-5 pkg. 2.8V LDO, TO-220-5 pkg. 3.0V LDO, TO-220-5 pkg.
Device	TC126	3 Fixed Output CN	MOS LDO with	Shutdown	d) e) a)	TC1263-5.0VAT	3.3V LDO, TO-220-5 pkg. 5.0V LDO, TO-220-5 pkg. 1.8V LDO, DDPAK-5 pkg.,
Voltage Option:*	2.5 2.8	= 2.5V = 2.8V			b)		Tape and Reel 2.5V LDO, DDPAK-5 pkg., Tape and Reel
	3.0 = 3.0V 3.3 = 3.3V 5.0 = 5.0V				c) d)		3.0V LDO, DDPAK-5 pkg., Tape and Reel 3.3V LDO, DDPAK-5 pkg.,
		r output voltages licrochip sales offic		Please contact your	a) b)	TC1263-2.5VOA TC1263-2.5VOATR	
Temperature Rang	ge: V =	-40°C to +125°C			c) d)	TC1263-2.8VOA TC1263-2.8VOATR	Tape and Reel 2.5V LDO, SOIC-8 pkg. 2.5V LDO, SOIC-8 pkg.,
Package	AT ET ETTR OA OATR	Plastic TransTape and RePlastic SOIC	istor Outline (D istor Outline (D el , (150 mil Body , (150 mil Body		e) f) g) h)	TC1263-3.0VOA TC1263-3.0VOATR TC1263-3.3VOA TC1263-3.3VOATR	
					i)	TC1263-5.0VOA	Tape and Reel 5.0V LDO, SOIC-8 pkg.

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NOTES:

Note the following details of the code protection feature on Microchip devices:

- Microchip products meet the specification contained in their particular Microchip Data Sheet.
- Microchip believes that its family of products is one of the most secure families of its kind on the market today, when used in the
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CERTIFIED BY DNV

ISO/TS 16949:2002

Microchip received ISO/TS-16949:2002 quality system certification for its worldwide headquarters, design and wafer fabrication facilities in Chandler and Tempe, Arizona and Mountain View, California in October 2003. The Company's quality system processes and procedures are for its PICmicro® 8-bit MCUs, KEELOQ® code hopping devices, Serial EEPROMs, microperipherals, nonvolatile memory and analog products. In addition, Microchip's quality system for the design and manufacture of development systems is ISO 9001:2000 certified.



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